

Excellent Integrated System Limited

Stocking Distributor

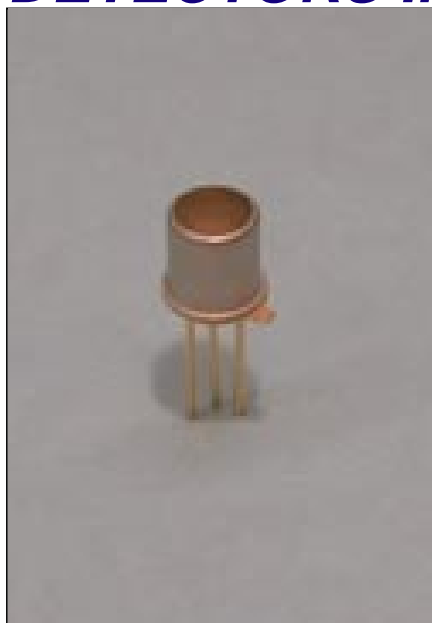
Click to view price, real time Inventory, Delivery & Lifecycle Information:

[Advanced Photonix, Inc.](#)
[PDB-C100](#)

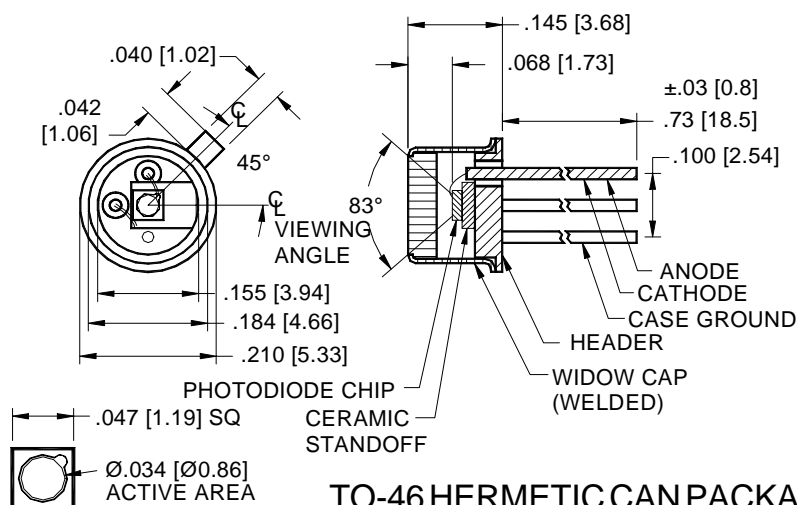
For any questions, you can email us directly:

sales@integrated-circuit.com

Silicon Photodiode, Blue Enhanced Photoconductive Isolated Type PDB-C100



PACKAGE DIMENSIONS inch [mm]



FEATURES

- High speed
- Low capacitance
- Isolated chip
- Low dark current

DESCRIPTION

The **PDB-C100** is a silicon, PIN planar diffused, blue enhanced photodiode. Ideal for high speed photoconductive & fiberoptic applications. Packaged in a hermetic TO-46 metal can with a flat window and isolated ground lead.

APPLICATIONS

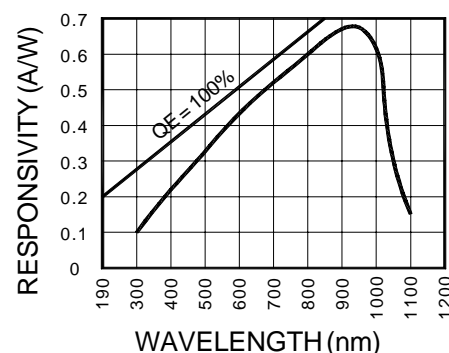
- Fiber optic
- Industrial controls
- Laser detection
- Particle detection

ABSOLUTE MAXIMUM RATING (TA=25°C unless otherwise noted)

| SYMBOL | PARAMETER | MIN | MAX | UNITS |
|------------------|-----------------------------|-----|------|-------|
| V _{BR} | Reverse Voltage | | 100 | V |
| T _{STG} | Storage Temperature | -55 | +150 | °C |
| T _O | Operating Temperature Range | -40 | +125 | °C |
| T _S | Soldering Temperature* | | +240 | °C |
| I _L | Light Current | | 0.5 | mA |

*1/16 inch from case for 3 secs max

SPECTRAL RESPONSE



ELECTRO-OPTICAL CHARACTERISTICS (TA=25°C unless otherwise noted)

| SYMBOL | CHARACTERISTIC | TEST CONDITIONS | MIN | TYP | MAX | UNITS |
|-------------------|----------------------------|---------------------------------|-----|----------------------|------|--------|
| I _{SC} | Short Circuit Current | H = 100 fc, 2850 K | 9 | 11 | | μA |
| I _D | Dark Current | H = 0, V _R = 15 V | | 1.0 | 2.0 | nA |
| R _{SH} | Shunt Resistance | H = 0, V _R = 10 mV | .50 | 5 | | GΩ |
| TCR _{SH} | RSH Temp. Coefficient | H = 0, V _R = 10 mV | | -8 | | % / °C |
| C _J | Junction Capacitance | H = 0, V _R = 15 V** | | 5 | 7 | pF |
| λ range | Spectral Application Range | Spot Scan | 400 | | 1150 | nm |
| λ _p | Spectral Response - Peak | Spot Scan | | 850 | | nm |
| V _{BR} | Breakdown Voltage | I = 10 μA | 100 | 125 | | V |
| NEP | Noise Equivalent Power | V _R = 15 V @ Peak | | 40x10 ⁻¹⁵ | | W/√Hz |
| tr | Response Time | RL = 50 Ω V _R = 15 V | | 3 | | nS |

Information in this technical data sheet is believed to be correct and reliable. However, no responsibility is assumed for possible inaccuracies or omission. Specifications are subject to change without notice. **f = 1MHz

[FORM NO. 100-PDB-C100 REV N/C]